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N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
100	0.105 at V _{GS} = 10 V	4.2		
	0.115 at V _{GS} = 4.5 V	3.9		

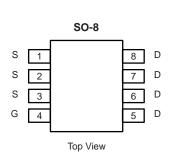
FEATURES

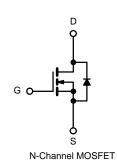
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g Tested



APPLICATIONS

- Load Switch
- LED Backlighting in LCD TVs





ABSOLUTE MAXIMUM RATINGS (T_C	= 25 °C, unless othe	rwise noted)			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	1-	4.2		
	T _C = 125 °C	l lD	3.2		
Pulsed Drain Current		I _{DM}	12.6	А	
Continuous Source Current (Diode Conduction)		I _S	4.5		
Avalanche Current		I _{AR}	4.5		
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E _{AR}	1.8	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	4.8 ^b	W	
	T _A = 25 °C] 'D [2.4 ^a] "	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
hungtion to Ambienta	t ≤ 10 s	R _{thJA}	40	51	°C/W
Junction-to-Ambient ^a	Steady State		18	25	
Junction-to-Case		R _{thJC}	2	2.4	

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static					l l		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80 V, V _{GS} = 0 V			1		
		$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$			50	μA	
		V _{DS} = 80 V, V _{GS} = 0 V, T _J = 175 °C			250	1	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V			12.6	Α	
		V _{GS} = 10 V, I _D = 2.7 A		0.105	0.117		
D : 0	D	V _{GS} = 10 V, I _D = 2.5 A, T _J = 125 °C			0.129	Ω	
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 2.5 A, T _J = 175 °C			0.134		
		V _{GS} = 4.5 V, I _D = 2.5 A		0.115	0.128		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 2.5 A		7		S	
Dynamic ^a							
Input Capacitance	C _{iss}			1561		pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 80 V, f = 1 MHz		110			
Reverse Transfer Capacitance	C _{rss}			65			
Total Gate Charge ^c	Q_g			7	11		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 80 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}$		2.1		nC	
Gate-Drain Charge ^c	Q _{gd}			2.6			
Gate Resistance	R _g			3		Ω	
Turn-On Delay Time ^c	t _{d(on)}			10		ns	
Rise Time ^c	t _r	$V_{DD} = 80 \text{ V}, R_L = 5 \Omega$ $I_D \cong 15 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$		16			
Turn-Off Delay Time ^c	t _{d(off)}			11			
Fall Time ^c	t _f			15			
Source-Drain Diode Ratings and Cha	racteristic (T	_C = 25 °C)					
Pulsed Current	I _{SM}				12.6	Α	
Diode Forward Voltage ^b	V_{SD}	$I_F = 15 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 15 A, dI/dt = 100 A/μs		50	80	ns	

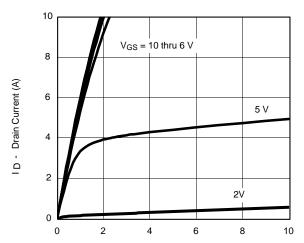
Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

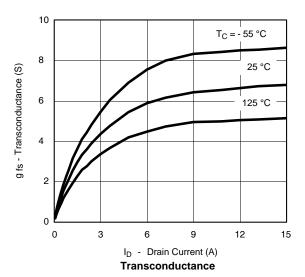


TYPICAL CHARACTERISTICS (25 °C unless noted)



V_{DS} - Drain-to-Source Voltage (V)





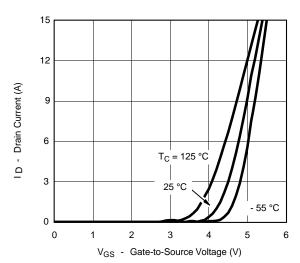
2000
1600
Ciss
1200
400
Crss
Coss

20

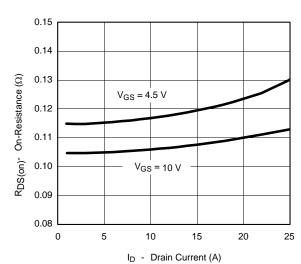
V_{DS} - Drain-to-Source Voltage (V) **Capacitance**

60

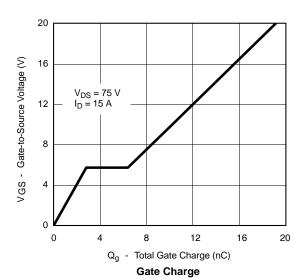
100



Transfer Characteristics

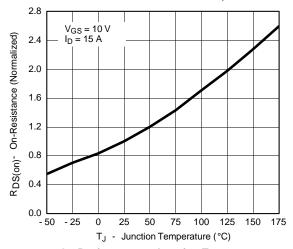


On-Resistance vs. Drain Current



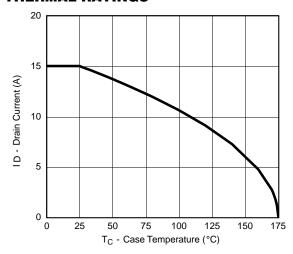


TYPICAL CHARACTERISTICS (25 °C unless noted)

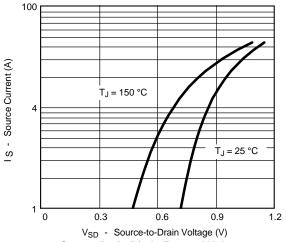


On-Resistance vs. Junction Temperature

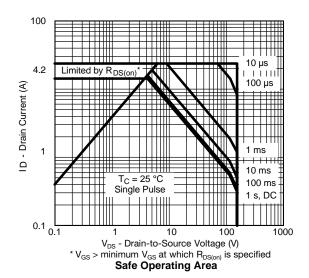
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



Source-Drain Diode Forward Voltage



Normalized Thermal Transient Impedance, Junction-to-Case

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